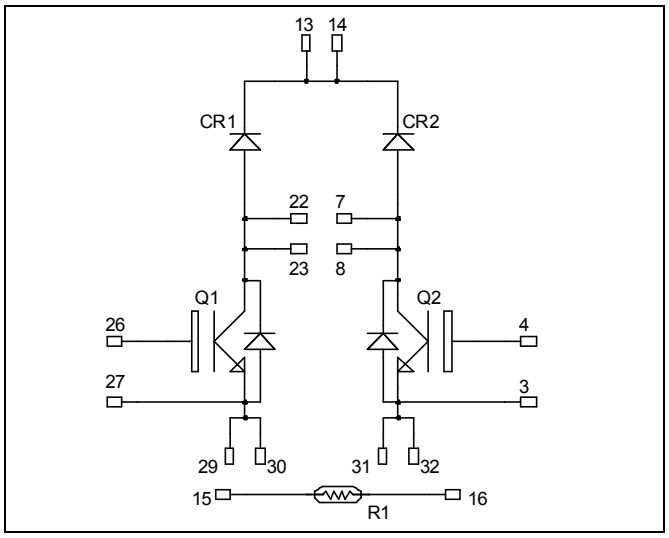
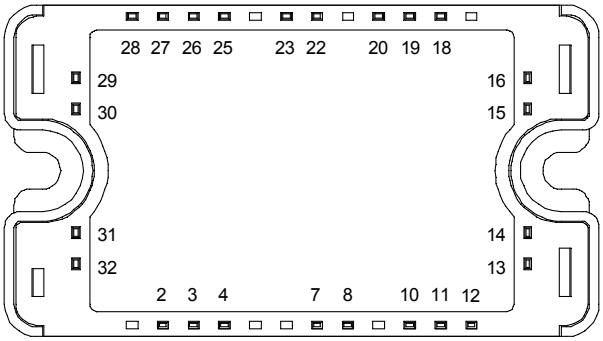
APTGT50DDA120T3G

Dual Boost chopper
Fast Trench + Field Stop IGBT3
Power Module

V_{CES} = 1200V
I_C = 50A @ Tc = 80°C





All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 …

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Fast Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- Each leg can be easily paralleled to achieve a single boost of twice the current capability.
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	T_C = 25°C	75	A
		T_C = 80°C	50	
I_{CM}	Pulsed Collector Current	T_C = 25°C	100	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	270	W
RBSOA	Reverse Bias Safe Operating Area	T_J = 125°C	100A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V V_{CE} = 1200V	T_j = 25°C			250	µA
			T_j = 125°C			500	
$V_{CE(sat)}$	Collector Emitter saturation Voltage	V_{GE} =15V I_C = 50A	T_j = 25°C	1.4	1.7	2.1	V
			T_j = 125°C		2.0		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 2mA		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				400	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V,V_{CE} = 25V f = 1MHz			3600		pF
C_{rss}	Reverse Transfer Capacitance				160		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 50A R_G = 18Ω			90		ns
T_r	Rise Time				30		
$T_{d(off)}$	Turn-off Delay Time				420		
T_f	Fall Time				70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 50A R_G = 18Ω			90		ns
T_r	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				520		
T_f	Fall Time				90		
E_{on}	Turn-on Switching Energy	V_{GE} = ±15V V_{Bus} = 600V I_C = 50A R_G = 18Ω	T_j = 125°C		5		mJ
E_{off}	Turn-off Switching Energy		T_j = 125°C		5.5		

Chopper diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1200V	T_j = 25°C			250	µA
			T_j = 125°C			500	
I_F	DC Forward Current		Tc = 70°C		60		A
V_F	Diode Forward Voltage	I_F = 60A			2	2.5	V
		I_F = 120A			2.3		
		I_F = 60A	T_j = 125°C		1.8		
t_{rr}	Reverse Recovery Time	I_F = 60A V_R = 800V di/dt =200A/µs	T_j = 25°C		400		ns
			T_j = 125°C		470		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		1200		nC
			T_j = 125°C		4000		
E_r	Reverse Recovery Energy	I_F = 60A V_R = 800V di/dt =1000A/µs	T_j = 125°C		2.2		mJ

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		50		kΩ
$B_{25/85}$	T_{25} = 298.15 K		3952		K

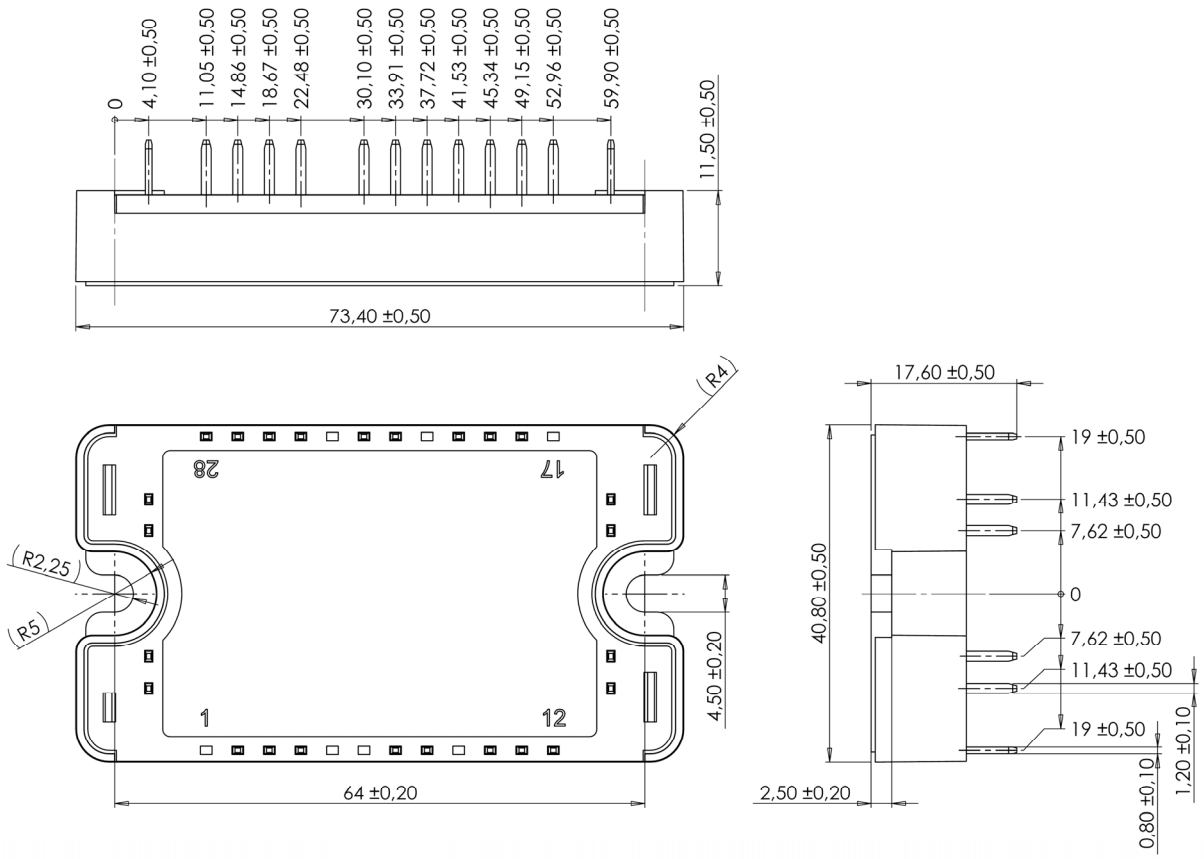
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.45	°C/W
			Diode			0.9	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

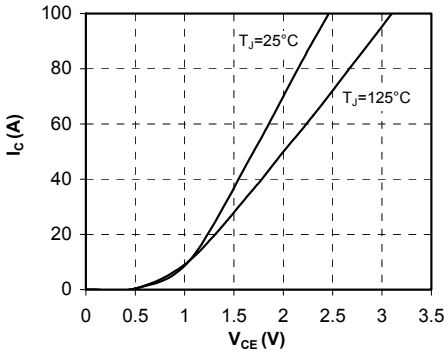
SP3 Package outline (dimensions in mm)



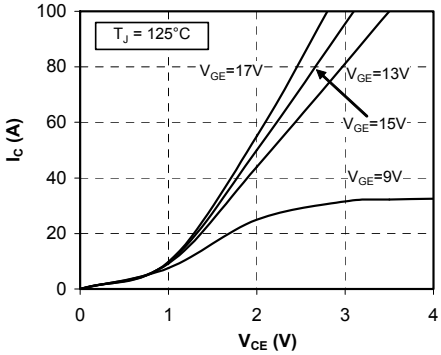
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve

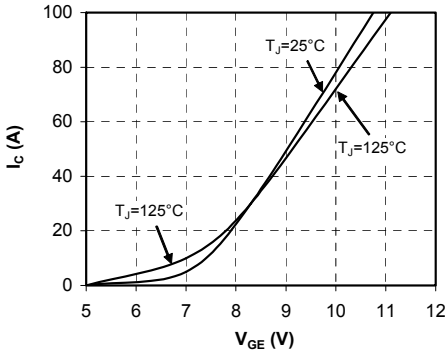
Output Characteristics (V_{GE}=15V)



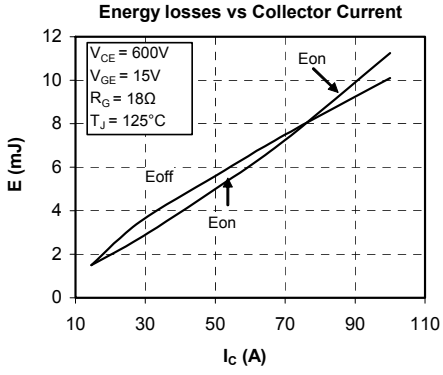
Output Characteristics



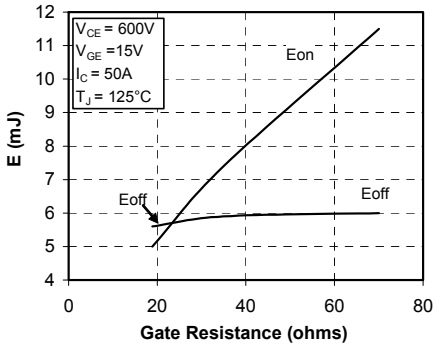
Transfert Characteristics



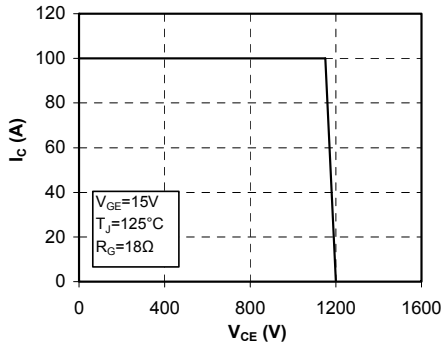
Energy losses vs Collector Current



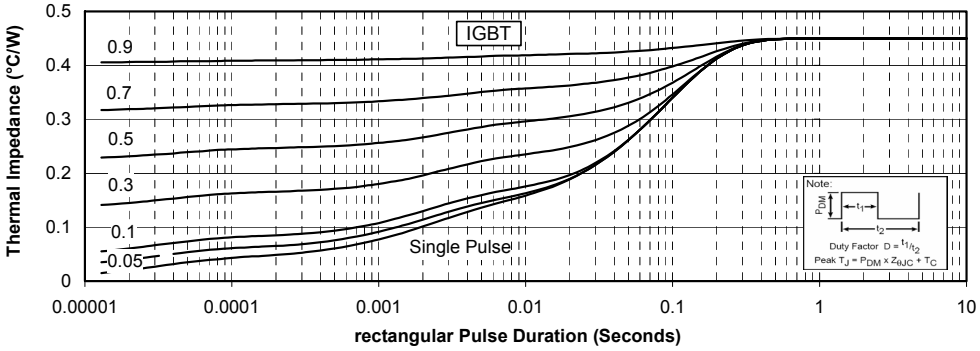
Switching Energy Losses vs Gate Resistance

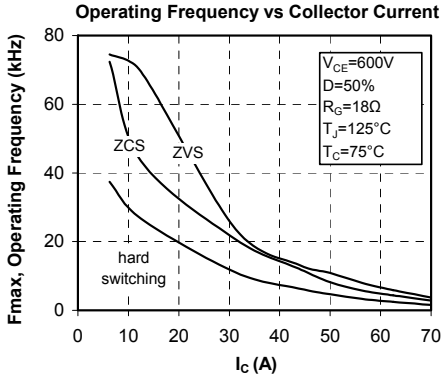


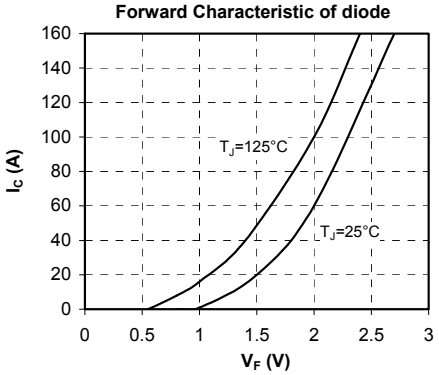
Reverse Bias Safe Operating Area

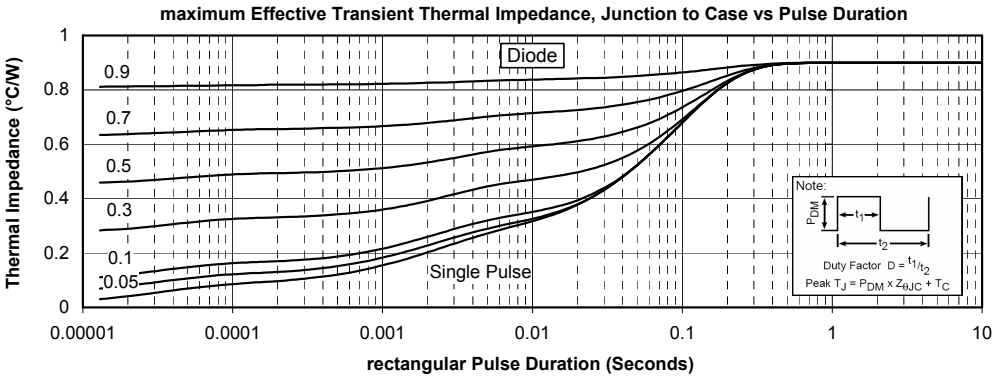


maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration




Operating Frequency vs Collector Current
Fmax, Operating Frequency (kHz)
80
60
40
20
0
0
10
20
30
40
50
60
70
I_C (A)
V_{CE}=600V
D=50%
R_G=18Ω
T_J=125°C
T_C=75°C
ZCS
ZVS
hard
switching


Forward Characteristic of diode
I_C (A)
160
140
120
100
80
60
40
20
0
0
0.5
1
1.5
2
2.5
3
V_F (V)
T_J=125°C
T_J=25°C


maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration
Thermal Impedance (°C/W)
1
0.8
0.6
0.4
0.2
0
0.00001
0.0001
0.001
0.01
0.1
1
10
rectangular Pulse Duration (Seconds)
Diode
0.9
0.7
0.5
0.3
0.1
0.05
Single Pulse
Note:
P_{DM}
t_1
t_2
Duty Factor D = t_1/t_2
Peak T_J = P_{DM} x $Z_{\theta JC}$ + T_C

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